

AMENDMENTS TO THE SPECIFICATION:

Please amend the specification by replacing the paragraph beginning on page 3, line 1 and extending to line 4 with the following new paragraph:

In the capacity type sensor according to the present invention, preferably the first electrode or the second electrode includes a plate type thin film portion which is constituted by a depression at the central part of lower side of the first or second electrode, ~~and the thin film portion is a vibrating electrode.~~

Please amend the specification by replacing the paragraph beginning on page 3, line 5 and extending to line 7 with the following new paragraph:

In the capacity type sensor according to the present invention, preferably the first electrode or the second electrode ~~which is formed as~~ including the thin film portion is a vibrating electrode.

Please amend the specification by replacing the paragraph beginning on page 3, line 14 and extending to line 20 with the following new paragraph:

A capacity type sensor in accordance with another aspect of the present invention includes: a first electrode and a second electrode which are opposedly disposed each other and an area of either one of the first electrode ~~and the~~ or second electrode is made narrower than another; and a first supporting member which is disposed outside of outer periphery of one of the electrodes with a narrower area to support another one of the electrodes with a wider area.

Please amend the specification by replacing the paragraph beginning on page 3, line 21 and extending to line 23 with the following new paragraph:

The capacity type sensor according to the present invention, preferably further includes a substrate, and the first supporting member supports the electrode with the wider area on the substrate.

Please amend the specification by replacing the paragraph beginning on page 3, line 24 and extending to line 28 with the following new paragraph:

In the capacity type sensor according to the present invention, preferably either one of the first [[and]] or the second electrode is disposed on the substrate, and ~~a third supporting member is~~ the sensor includes a second supporting member disposed between the substrate and ~~another~~ either one of the electrode which is [[not]] disposed on the substrate.

Please amend the specification by replacing the paragraph beginning on page 3, line 29 and extending to line 32 with the following new paragraph:

In the capacity type sensor according to the present invention, preferably an opening portion is formed at the central part of the substrate, and the electrode formed on the ~~third~~ second supporting member is a vibrating electrode.

Please amend the specification by replacing the two paragraphs beginning on page 3, line 33 and extending to page 4 line 6 with the following new paragraph:

~~In the capacity type sensor according to the present invention, preferably either one of the first and the second electrode is disposed on another one of electrode and a forth supporting member is included between the both electrodes.~~

~~The capacity type sensor according to the present invention, preferably further includes a fifth supporting member which is formed on the electrode with a wider area, and an insulating member which is supported by the fifth supporting member, and the electrode with a narrower area is formed on the insulating member.~~

A capacity type sensor in accordance with still another aspect of the present invention includes: a first electrode with wider area; a second electrode with narrower area which is disposed on the first electrode with the wider area; a third supporting member which is formed on the first electrode with the wider area; and a fourth supporting member which is supported by the third supporting member, wherein the second electrode with the narrower area is formed on the fourth supporting member.

Please amend the specification by replacing the paragraph beginning on page 4, line 7 and extending to line 12 with the following new paragraph:

The capacity type sensor according to the present invention, preferably further includes: a guard electrode which is disposed between the first supporting member and second supporting member or between the third supporting member and fourth supporting member~~fifth supporting member and the insulating member~~; a potential equalizer to make the potential difference between the first electrode and the guard electrode close to zero; and a capacity type sensor detector to detect impedance change between the first electrode and the second electrode.

Please amend the specification by replacing the paragraphs beginning on page 12, line 3 and extending to line 15 with the following new paragraph:

A substrate 8 shown in Fig. 11 (a) is formed out of single crystal silicon substrate which is, for example, substantially square and has comparatively large thickness, and a rectangular opening portion 81 is formed at the central part of the substrate. An insulating material 3a as the second supporting member is made out of, for example, silicon oxide film on the whole substrate 8 other than the opening portion 81 as shown in Fig. 11 (b). As shown in Fig. 11 (c), a second electrode 2b with a circular shape is formed out of, for example, single crystal silicon so as to have smaller diameter than that of the opening portion 81. From one part of the second electrode an extended portion 24 is formed so as to extend on the insulating material 3a, and the second electrode pad, not shown in the drawing, is formed on a tip part of the extended portion. The first electrode 1a functions as the fixed electrode and the second electrode 2b functions as the vibrating electrode.

Please amend the specification by replacing the paragraphs beginning on page 12, line 16 and extending to line 24 with the following new paragraph:

Further, four insulating materials 5a as the first supporting members with comparatively large thickness, are formed out of silicon oxide film, along each edge of the substrate 8 outside of outer periphery of the second electrode 2b on the insulating material 3a as shown in Fig. 11 (d). These insulating materials 5a function as fixing members to fix the first electrode 1a. Moreover, as shown in Fig. 11 (e), the first electrode 1a is made out of polycrystalline silicon film so as to be held by the insulating

material 5a. The first electrode 1a has a larger diameter than the second electrode 2b in order to cover four insulating materials 5a.

Please amend the specification by replacing the paragraphs beginning on page 14, line 1 and extending to line 10 with the following new paragraph:

In this ninth embodiment, a substrate which has a comparatively large thickness is utilized as a second electrode 2c ~~a second electrode 2c is formed by the substrate which has comparatively large thickness~~ as shown in Fig. 14 (e), and an insulating material 3c is formed on the second electrode 2c except on the periphery and the circular shape portion at the center as shown in Fig. 14 (b). An insulating material 5b is formed on the insulating material 3c as shown in Fig. 14 (c), and a first electrode 1b is formed on the insulating material 5b in the same manner as the embodiments shown in Fig. 11 to Fig. 13. On the first electrode 1b, an extended portion 13 is formed so as to be connected to the first electrode pad which is not shown in the drawing. The insulating materials 3c and 5b constitute ~~fourth~~ third supporting members.

Please amend the specification by replacing the paragraphs beginning on page 15, line 7 and extending to line 15 with the following new paragraph:

In this eleventh embodiment, a guard electrode 4c shown in Fig. 16 (c) is formed between the insulating materials 3d shown in Fig. 16 (b) as ~~fifth~~ the third supporting members and an insulating material 5e shown in Fig. 16 (d) as ~~an insulating~~ the fourth supporting member. This guard electrode 4c has the same function as the guard electrodes which are provided so as to reduce the parasitic capacity in the

embodiments explained with reference to Fig. 1 to Fig. 10. Further by applying the electrical connections shown in Fig. 3 to Fig. 6, the sensitivity can be improved and at the same time the input conversion noise level can be reduced.